



# PCD20065V

## 650V Silicon Carbide Diode

### Features

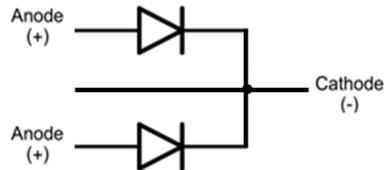
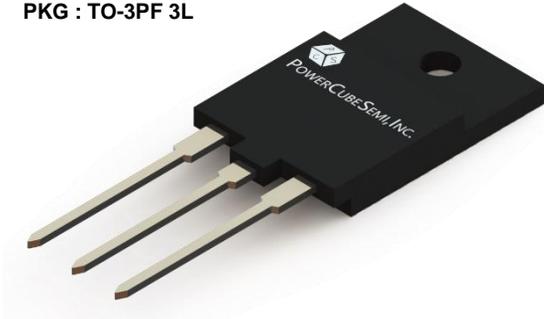
- 650-Volt Schottky Rectifier
- Shorter recovery time
- High-speed switching possible
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- Positive Temperature Coefficient on VF
- RoHS Compliant

### Applications

- Switch Mode Power Supplies
- Power Factor Correction
- Motor Drives
- Uninterruptible Power Supply
- Solar Inverter
- EV Charger

### Package Outline

PKG : TO-3PF 3L



### Absolute Maximum Ratings

T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>RRM</sub>	Repetitive Peak Reverse Voltage	650	V
V <sub>RSM</sub>	Surge Peak Reverse Voltage	650	V
V <sub>DC</sub>	DC Blocking Voltage	650	V
I <sub>F</sub>	Continuous Forward Current T <sub>C</sub> = 25°C T <sub>C</sub> = 95°C	14 / 28 10 / 20	A
I <sub>FRM</sub>	Repetitive Peak Forward Current T <sub>C</sub> = 110°C	36 / 72	A
I <sub>FSM</sub>	Non-Repetitive Forward Surge Current (PW=10ms sinusoidal) T <sub>C</sub> = 25°C T <sub>C</sub> = 110°C	80 / 160 64 / 128	A
P <sub>D</sub>	Power Dissipation T <sub>C</sub> = 25°C	34 / 68	W
T <sub>J</sub> , T <sub>stg</sub>	Operating Junction and Storage Temperature	-55 to +175	°C

\* Per Leg / Per Device

## Electrical Characteristics (Per Leg)

$T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$V_F$	Forward Voltage	$I_F = 10\text{A}, T_C = 25^\circ\text{C}$ $I_F = 10\text{A}, T_C = 175^\circ\text{C}$	--	1.45 2.0	1.75 2.4	V
$I_R$	Reverse Current	$V_R = 650\text{V}, T_C = 25^\circ\text{C}$ $V_R = 650\text{V}, T_C = 175^\circ\text{C}$	--	5 25	100 -	$\mu\text{A}$
$Q_C$	Total Capacitive Charge	$V_R = 400\text{V}$	--	39	--	nC
C	Total Capacitance	$V_R = 1\text{V}, T_J = 25^\circ\text{C}, f = 1\text{MHz}$ $V_R = 520\text{V}, T_J = 25^\circ\text{C}, f = 1\text{MHz}$	--	467 67	--	pF

## Thermal Characteristics

$T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Min	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	4.4 / 2.2	5.3 / 2.6	$^\circ\text{C}/\text{W}$

\* Per Leg / Per Device

## Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
P2CD20065V	P2CD20065	TO-3PF-3L	-	-	30

\* P2DCD20065V : RoHS Compliant

## Typical Characteristics (Per Leg)

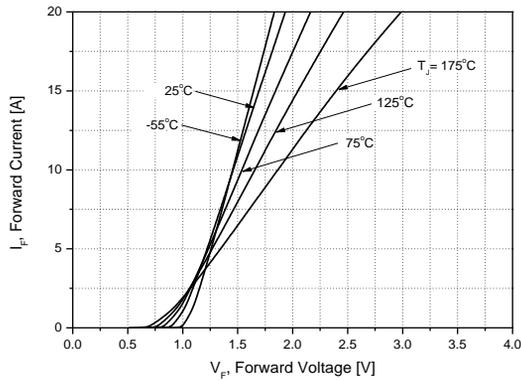


Figure 1. Forward Characteristics

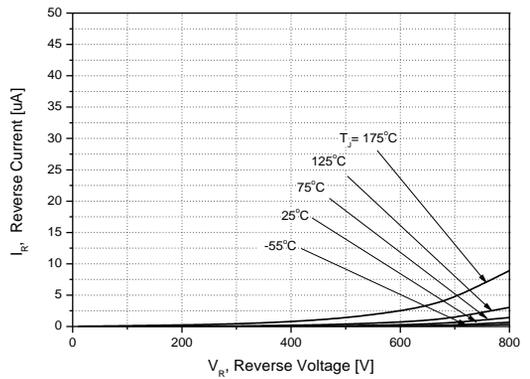


Figure 2. Reverse Characteristics

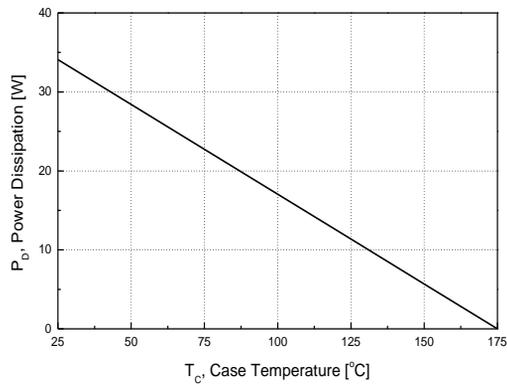


Figure 3. Power Dissipation

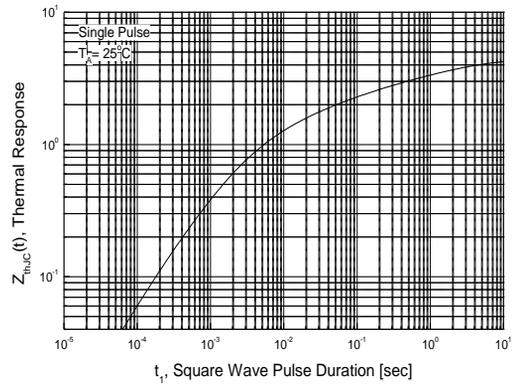


Figure 4. Transient Thermal Resistance

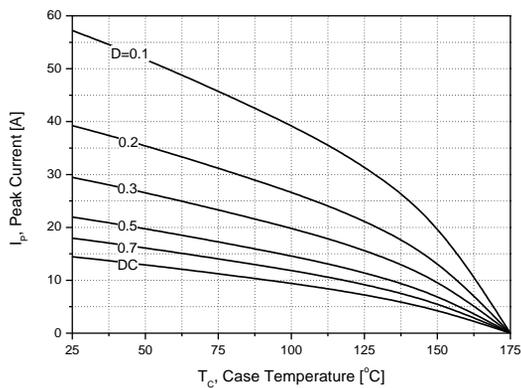


Figure 5. Peak Forward Current Derating

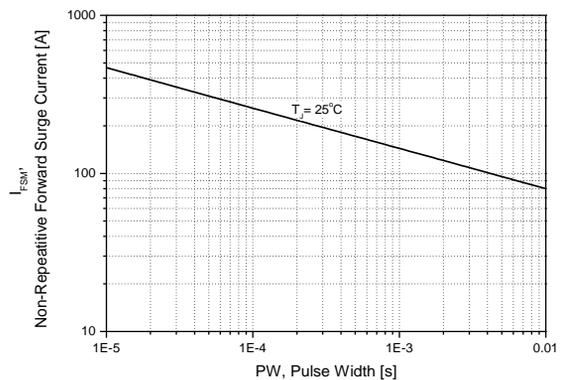


Figure 6. Non-Repetitive Peak Forward Surge Current vs. Pulse Duration

## Typical Characteristics (Per Leg)

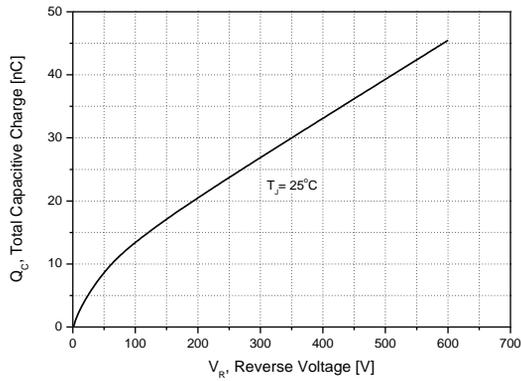


Figure 7. Total Capacitive Charge

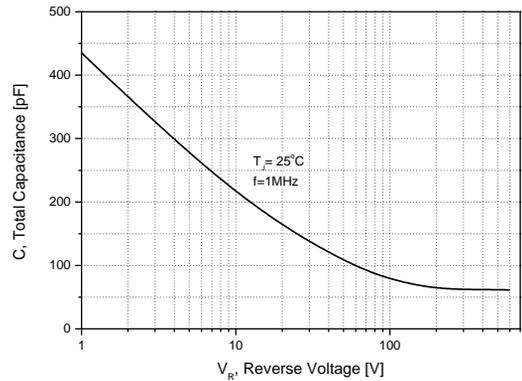


Figure 8. Total Capacitance

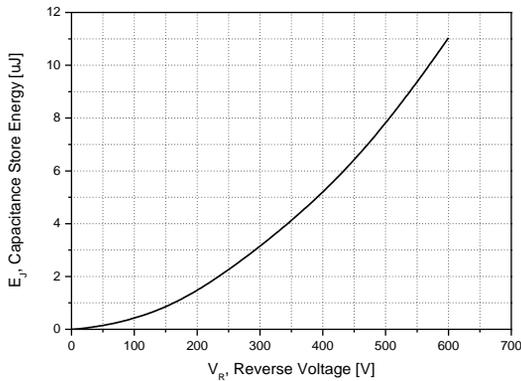


Figure 9. Capacitance Store Energy

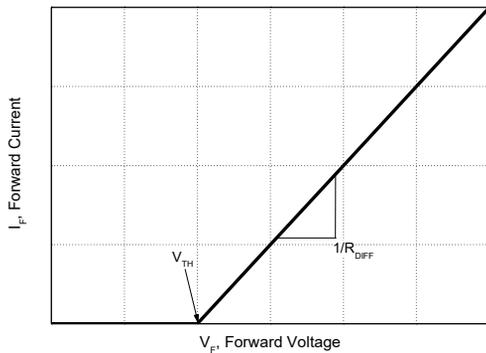


Figure 10. Equivalent Forward Current Curve

$$V_F = V_{TH} + R_{DIFF} \times I_F$$

### Threshold Voltage ( $V_{TH}$ )

$$V_{TH}(T_j) = -0.001 \times (T_j) + 0.950 \text{ [V]}$$

### Differential Resistance ( $R_{DIFF}$ )

$$R_{DIFF}(T_j) = A \times T_j^2 + B \times T_j + C \text{ [\Omega]}$$

$$A = 5.92 \times 10^{-7}$$

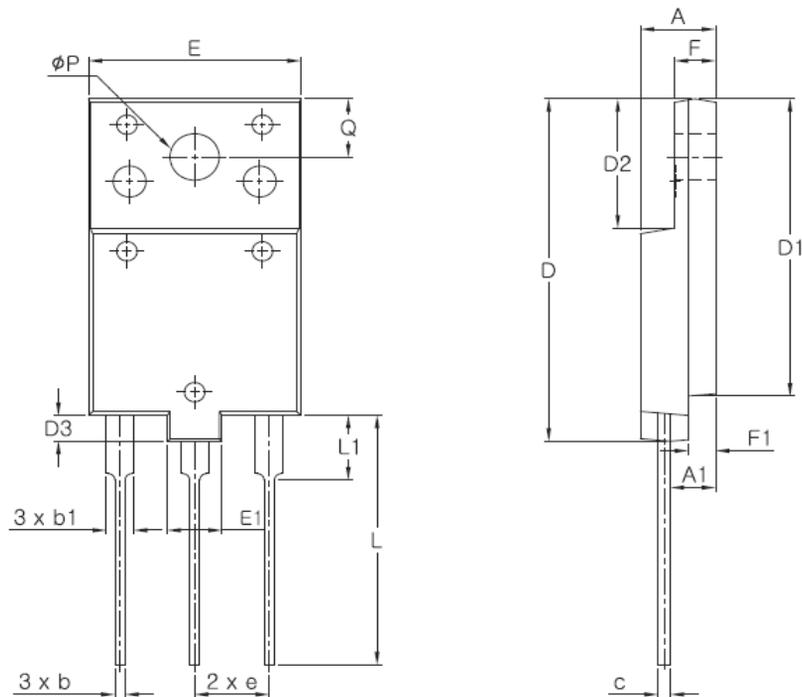
$$B = 2.27 \times 10^{-4}$$

$$C = 4.17 \times 10^{-2}$$

$$[T_j \text{ [}^\circ\text{C]}; -55^\circ\text{C} \leq T_j \leq 175^\circ\text{C}; I_F \leq 10 \text{ A}]$$

# Package Information

TO-3PF-3L



SYMBOL	MIN	NOM	MAX
A	5.30	5.50	5.70
A1	3.10	3.30	3.50
b	0.65	0.75	0.85
b1	1.80	2.00	2.20
c	0.80	0.90	1.00
D	26.30	26.50	26.70
D1	22.80	23.00	23.20
D2	9.80	10.00	10.20
D3	1.80	2.00	2.20
E	15.30	15.50	15.70
E1	3.80	4.00	4.20
e	* 5.15	* 5.45	* 5.75
F	2.80	3.00	3.20
F1	1.80	2.00	2.20
L	19.10	19.30	19.50
L1	4.80	5.00	5.20
Q	4.30	4.50	4.70
$\phi P$	3.40	3.60	3.80

NOTE

1. THESE DIMENSIONS DO NOT INCLUDE PROTRUSIONS OF THE M
2. THE "( )" MARK IS THE REFERENCE